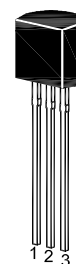


ST 2SA928

PNP Silicon Epitaxial Planar Transistor

for audio power amplifier

The transistor is subdivided into two groups, O and Y, according to its DC current gain.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter Symbol		Value	Unit
Collector Base Voltage	$-V_{CBO}$	30	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$ 2		A
Power Dissipation	P_{tot} 1		W
Junction Temperature	T_j 150		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter Symbol		Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 500\text{ mA}$	Current Gain Group O	h_{FE} 100	-	200	-
	Y	h_{FE} 160	-	320	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	--	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	30	--		V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	30	--		V
Emitter Base Breakdown Voltage at $-I_E = 1\text{ mA}$	$-V_{(BR)EBO}$	5	--		V
Collector Emitter Saturation Voltage at $-I_C = 1.5\text{ A}$, $-I_B = 30\text{ mA}$	$-V_{CE(sat)}$	--	-	2	V
Base Emitter Voltage at $-V_{CE} = 2\text{ V}$, $-I_C = 500\text{ mA}$	$-V_{BE}$	-	-	1	V
Gain Bandwidth Product at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	f_T	-	120	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	- 48	-		pF